

## ABSTRACT OF THE DISCLOSURE

Described is a polishing technique adapted for multilevel metallization of an electronic circuit device, which comprises  
5 polishing a metal film with a polishing liquid containing an oxidizing substance, a phosphoric acid and a protection-layer forming agent. The present invention makes it possible to polishing a metal film at a high removal rate while suppressing occurrence of scratches, delamination, dishing or erosion.

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